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Technical Program

MONDAY, MAY 21, 2001

8:00 am–10:00 am

Ballroom

SESSION MON1A: RFIC PLENARY: WIRELESS LAN, ADVANCES IN RF CMOS

Chair: D. Lovelace, *Gain Technology*

Co-Chair: S. Kiaei, *Arizona State University*

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8:30 am	T.H. Meng and B. McFarland, <i>Atheros Communications, Inc.</i>	
MON1A-2	Keynote Paper: Recent Advances in RF CMOS	Paper not available at time of printing
9:15 am	A. Hajimiri, <i>Cal Tech. University</i>	

MONDAY, MAY 21, 2001

10:20 am–12:00 pm

Ballroom

SESSION MON2A: W-CDMA TRANCEIVERS

Chair: N. Camilleri, *RF & Wireless Design Services*

Co-Chair: S. Heinen, *Infineon Technologies*

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11:00 am	B. Sam and P. Halford*, <i>Analog Devices, Inc., NW Labs, Beaverton, OR; *Analog Devices, Inc., ALP, Wilmington, MA</i>	
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11:40 am	W. Thomann, J. Fenk*, R. Hagelauer†, and R. Weigel‡, <i>DICE GmbH, Linz, Austria; *Infineon Technologies AG, München, Germany; †University of Linz, Research Institute of Integrated Circuits, Austria; ‡University of Linz, Institute for Communications and Information Engineering, Austria</i>	

MONDAY, MAY 21, 2001

10:20 am –11:40 am

Room Tucson 38–39

SESSION MON2B: POWER AMPLIFIERS: TECHNOLOGY & PERFORMANCE

Chair: B. Thompson, *Motorola, Inc.*

Co-Chair: F. Ali, *Nokia Mobile Phones*

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Room Tucson 40–41

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Chair: A. Jerng, *DSP Group*

Co-Chair: Y. Deval, *Laboratoire IXL*

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MONDAY, MAY 21, 2001

10:20 am–11:40 am

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Chair: K. Ashby, *Microtone Inc.*

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MONDAY, MAY 21, 2001

1:30 pm–3:00 pm

Ballroom

SESSION MON3A: GPS & BLUETOOTH SYSTEM DESIGN

Chair: R. Harjani, *University of Minnesota*

Co-Chair: J. Choma, *University of Southern California*

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MONDAY, MAY 21, 2001

3:50 pm–5:10 pm

Ballroom

SESSION MON4A: INTEGRATED BLUETOOTH TRANSCEIVERS

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Co-Chair: D. Allsot, *University of Washington*

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*Infineon Technologies AG, Design Center Düsseldorf, Germany; †University of Dortmund, Germany; ‡Ruhr-Universität Bochum, Germany
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Y.-H. Chen, J.-C. Bor*, and P.-C. Huang†, *SoC Technology Center, Industrial Technology Research Institute, HsinChu, Taiwan; *Advance Technology Division II, MediaTek Inc., HsinChu, Taiwan; †Circuit Design Engineering Division, MediaTek Inc., HsinChu, Taiwan*

MONDAY, MAY 21, 2001

3:30 pm–5:10 pm
Room Tucson 38–39

SESSION MON4B: RFIC PACKAGING & PASSIVE COMPONENTS

Chair: J. Staudinger, *Motorola SPS*

Co-Chair: M. Kumar, *Lockheed Martin Government Electronic Systems*

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MONDAY, MAY 21, 2001

3:30 pm–5:10 pm

Room Tucson 40–41

SESSION MON4C: ACTIVE DEVICE MODELING FOR RFIC APPLICATIONS

Chair: L. Liu, *TRW*

Co-Chair: V. Nair, *Motorola, Inc.*

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MONDAY, MAY 21, 2001

3:30 pm–5:10 pm
Room Tucson 42–43

SESSION MON4D: HIGH FREQUENCY DEVICES & IC TECHNIQUES

Chair: J. Mondal, *Motorola, Inc.*

Co-Chair: A. Gupta, *ANADIGICS, Inc.*

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*Department of Electrical & Computer Eng., University of Toronto, ON, Canada; *Nortel*
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M. Ju*, and H. Seo*, *Microwave and Systems Research Group, University of Surrey,*
*Guildford, UK; *Semiconductor Division, EONCOM, Ltd., Korea; †now at the University*
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Electronics, FMI, Kista, Sweden; †Hitachi Ltd., Device Development Center, Tokyo,
Japan; ‡Ericsson Microwave Systems AB, MHSERC, Mölndal, Sweden; §Present
address: Maxim Integrated Products, Design Center Hanover, Hanover, Germany

TUESDAY, MAY 22, 2001

1:20 pm–3:00 pm

Ballroom

SESSION TUE3A: RF TRANSCEIVERS

Chair: S. Heinen, *Infineon Technologies*

Co-Chair: N. Camilleri, *RF & Wireless Design Services*

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TUESDAY, MAY 22, 2001

1:20 pm–3:00 pm

Room Yuma 21–23

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Chair: F. Ali, *Nokia Mobile Phones*

Co-Chair: B. Thompson, *Motorola, Inc.*

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TUESDAY, MAY 22, 2001

3:30 pm–4:50 pm

Ballroom

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Chair: S. Lloyd, *Conexant Systems, Inc.*

Co-Chair: K. Ashby, *Microtune Inc.*

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TUESDAY, MAY 22, 2001

3:30 pm–5:10 pm

Room Yuma 21–23

SESSION TUE4F: BUILDING BLOCK FRONT ENDS

Chair: S. Lloyd, *Conexant Systems, Inc.*

Co-Chair: K. Ashby, *Microtone, Inc.*

TUE4F-1 3:30 pm	1.8V RF AGC and Mixer Implemented with a Novel Four-Terminal HBT (FHBT) S. Zhou, P. Ma, L. Zhang, P. Zampardi*, J. Li, Y.S. Chang†, and M.F. Chang, <i>Electrical Engineering Department, University of California, Los Angeles, CA</i> ; *Conexant Systems, Newbury Park, CA; †National Tsing-Hua University, Taiwan, ROC	241
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TUESDAY, MAY 22, 2001

2:30 pm–5:00 pm

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SESSION TUIF: (JOINT RFIC-IMS SESSION) INTERACTIVE FORUM

Chair: P. Okrah, *Motorola*

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